

**Inchange Semiconductor**

**Product Specification**

**Silicon PNP Power Transistors**

**2SA1141**

**DESCRIPTION**

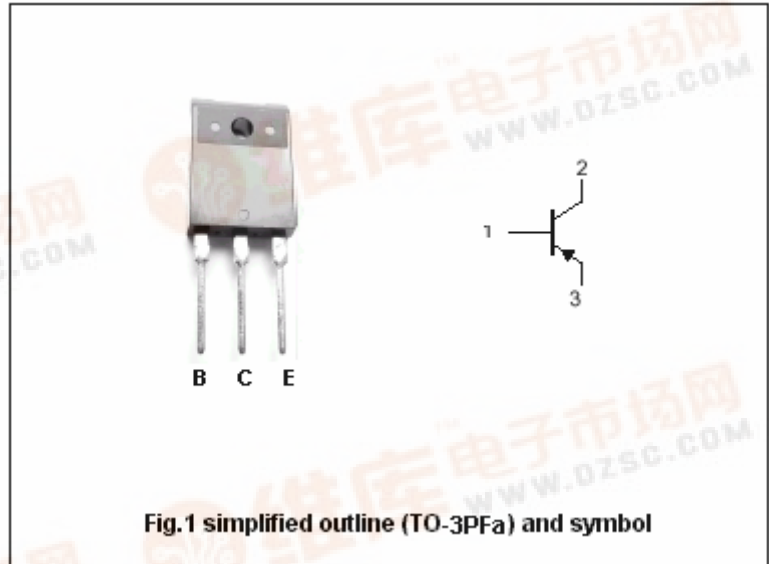
- With TO-3PFa package
- Complement to type 2SC2681
- High transition frequency

**APPLICATIONS**

- Audio frequency power amplifier
- High frequency power amplifier

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-115	V
$V_{CEO}$	Collector-emitter voltage	Open base	-115	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-10	A
$I_{CM}$	Collector current-peak		-15	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	100	W
		$T_a=25^\circ\text{C}$	2	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4.5A ; I <sub>B</sub> =-0.45A		-0.7	-1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-4.5A ; V <sub>CE</sub> =-2V		-1.2	-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V	60		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4.5A ; V <sub>CE</sub> =-2V	40			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=1MHz		390		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V		90		MHz

◆ h<sub>FE-1</sub> classifications

R	Q
60-120	100-200

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PACKAGE OUTLINE

